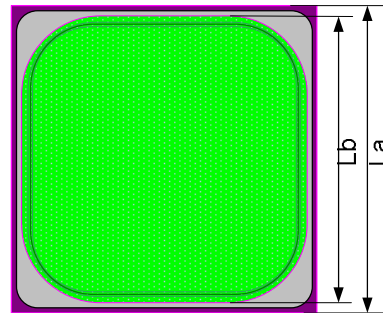


2SB082020MAJL SCHOTTKY BARRIER DIODE CHIPS
DESCRIPTION

- Ø 2SB082020MAJL is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits.;
- Ø Chip Size:830 μ m X 830 μ m;
- Ø Chip Thickness: 210 \pm 20 μ m;



Chip Topography and Dimensions

 La: Chip Size: 830 μ m;

 Lb: Pad Size: 750 μ m;

ORDERING SPECIFICATIONS

Product Name	Specification
2SB082020MAJL	For Au and AlSi wire bonding package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	20	V
Average Forward Rectified Current	IFAV	1	A
Peak Forward Surge Current@8.3ms	IFSM	40	A
Maximum Operation Junction Temperature	TJ	150	$^{\circ}$ C
Storage Temperature Range	TSTG	-40~150	$^{\circ}$ C

ELECTRICAL CHARACTERISTICS (Tamb=25 $^{\circ}$ C)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=50 μ A	20	--	V
Forward Voltage	VF1	IF=1A	--	0.530	V
	VF2	IF=2A	--	0.595	V
Reverse Current	IR1	VR=20V	--	10	μ A
	IR2	VR=10V	--	1	μ A